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Арр	lication No.	Applicant(s)
	43,967	NANSEI ET AL.
	miner	Art Unit
Toni	iae M. Thomas	2822
The MAILING DATE of this communication appears o	on the cover sheet wi	th the correspondence address.
Il claims being allowable, PROSECUTION ON THE MERITS IS (OR Ferewith (or previously mailed), a Notice of Allowance (PTOL-85) or oth OTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHTS the Office or upon petition by the applicant. See 37 CFR 1.313 and I	REMAINS) CLOSED in ner appropriate commu S. This application is s	n this application. If not included unication will be mailed in due course. THIS
. A This communication is responsive to the request for reconsiderate	tion filed 22 Aug 2005	
. ☑ The allowed claim(s) is/are <u>1,3-11,39 and 40</u> .		
<ul> <li>.          ☐ Acknowledgment is made of a claim for foreign priority under 3</li> <li>a)        ☐ All b)        ☐ Some* c)        ☐ None of the:</li> </ul>	5 U.S.C. § 119(a)-(d) (	or (f).
<ol> <li>Certified copies of the priority documents have been</li> </ol>	received.	
<ol><li>Certified copies of the priority documents have been</li></ol>	received in Application	on No 🤈
3.  Copies of the certified copies of the priority document	nts have been received	d in this national stage application from the
International Bureau (PCT Rule 17.2(a)).		
* Certified copies not received:		
Applicant has THREE MONTHS FROM THE "MAILING DATE" of this noted below. Failure to timely comply will result in ABANDONMENT THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.	communication to file of this application.	a reply complying with the requirements
. A SUBSTITUTE OATH OR DECLARATION must be submitted. INFORMAL PATENT APPLICATION (PTO-152) which gives real	Note the attached EXA	AMINER'S AMENDMENT or NOTICE OF declaration is deficient.
CORRECTED DRAWINGS (as "replacement sheets") must be s	ubmitted.	
(a) including changes required by the Notice of Draftsperson's F		v ( PTO-948) attached
1) ☐ hereto or 2) ☐ to Paper No./Mail Date	•	
(b) ☐ including changes required by the attached Examiner's Ame Paper No./Mail Date	ndment / Comment or	in the Office action of
Identifying indicia such as the application number (see 37 CFR 1.84(c)) each sheet. Replacement sheet(s) should be labeled as such in the hea	should be written on the	ne drawings in the front (not the back) of R 1.121(d).
DEPOSIT OF and/or INFORMATION about the deposit of attached Examiner's comment regarding REQUIREMENT FOR T	BIOLOGICAL MATE THE DEPOSIT OF BIO	ERIAL must be submitted. Note the DLOGICAL MATERIAL.
ttachment(s)		
. ☑ Notice of References Cited (PTO-892)	5. Notice of Inf	formal Patent Application (PTO-152)
☐ Notice of Draftperson's Patent Drawing Review (PTO-948)	6. ☐ Interview St	ummary (PTO-413),
☐ Information Disclosure Statements (PTO-1449 or PTO/SB/08), Paper No./Mail Date		Mail Date Amendment/Comment
Examiner's Comment Regarding Requirement for Deposit of Biological Material	8. 🛭 Examiner's	Statement of Reasons for Allowance
	9.	- coordant continued on con-
		Mary Wilczewski

Application/Control Number: 10/643,967

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### **EXAMINER'S AMENDMENT**

## Election/Restrictions

1. This application is in condition for allowance except for the presence of claims 12-38 non-elected without traverse. Accordingly, claims 12-38 have been cancelled.

#### **Amendment**

2. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

The application has been amended as follows:

# In Claims

Claims 12-38 have been cancelled.

## Reasons for Allowance

3. The following is an examiner's statement of reasons for allowance: the prior art of record does not anticipate or render obvious a method for manufacturing a semiconductor device substantially as claimed. For example, it is known to form a lower silicon oxide film, form a silicon film on the lower silicon oxide film, and completely nitride the silicon film by a plasma nitriding method, thereby forming a silicon nitride film on the lower silicon oxide film, as evidenced by Weimer (US 2003/0040171 A1). However, the prior art of record does not anticipate, teach or suggest - either separately or combined - a

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method for manufacturing a semiconductor device substantially as claimed, wherein the method comprises: completely nitriding the silicon film with a surface wave plasma generated by a plasma nitriding method to form the silicon nitride film, and further forming an upper silicon oxide film on the silicon nitride film by a plasma oxidizing method, as recited in claim 1; forming an upper silicon oxide film on the silicon nitride film by a plasma oxidizing method, wherein the plasma oxidizing method forms a gate insulation film composed of only silicon oxide in a peripheral circuit region simultaneously with the upper silicon oxide film, as recited in claim 40; and forming the silicon film on the lower silicon oxide film to a thickness of 5 nm or above, as recited in claim 39.1

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Toniae M. Thomas whose telephone number is (571) 272-1846. The examiner can normally be reached on Monday through Friday from 8:30 a.m. to 5:30 p.m.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Zandra Smith can be reached on (571) 272-2429. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

<sup>&</sup>lt;sup>1</sup> The silicon film has a thickness of less than 30 Å, i.e. 3 nm (par. 24, lines 11-13).

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

TMT 13 November 2005

> Mary Wilczewski Primary Examiner

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